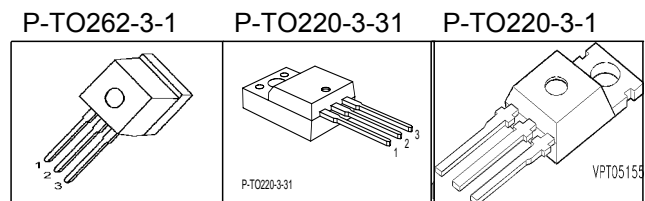


Cool MOS™ Power Transistor

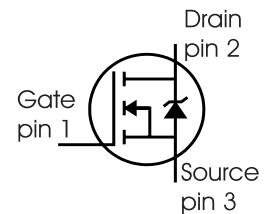
Feature

- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- High peak current capability
- Improved transconductance

| | | |
|--------------|------|----------|
| V_{DS} | 650 | V |
| $R_{DS(on)}$ | 0.38 | Ω |
| I_D | 11 | A |



| Type | Package | Ordering Code | Marking |
|------------|--------------|---------------|---------|
| SPP11N65C3 | P-TO220-3-1 | Q67040-S4557 | 11N65C3 |
| SPA11N65C3 | P-TO220-3-31 | Q67040-S4554 | 11N65C3 |
| SPI11N65C3 | P-TO262-3-1 | Q67040-S4561 | 11N65C3 |



Maximum Ratings

| Parameter | Symbol | Value | | Unit |
|---|----------------|------------|-------------------------------------|-------------|
| | | SPP_I | SPA | |
| Continuous drain current $T_C = 25\text{ °C}$ $T_C = 100\text{ °C}$ | I_D | 11 7 | 11 ¹⁾ 7 ¹⁾ | A |
| Pulsed drain current, t_p limited by T_{jmax} | I_D puls | 33 | 33 | A |
| Avalanche energy, single pulse $I_D=2.5A, V_{DD}=50V$ | E_{AS} | 340 | 340 | mJ |
| Avalanche energy, repetitive t_{AR} limited by T_{jmax} ²⁾ $I_D=4A, V_{DD}=50V$ | E_{AR} | 0.6 | 0.6 | |
| Avalanche current, repetitive t_{AR} limited by T_{jmax} | I_{AR} | 4 | 4 | A |
| Gate source voltage | V_{GS} | ± 20 | ± 20 | V |
| Gate source voltage AC ($f > 1\text{Hz}$) | V_{GS} | ± 30 | ± 30 | |
| Power dissipation, $T_C = 25\text{ °C}$ | P_{tot} | 125 | 33 | W |
| Operating and storage temperature | T_j, T_{stg} | -55...+150 | | °C |

Maximum Ratings

| Parameter | Symbol | Value | Unit |
|---|---------|-------|------|
| Drain Source voltage slope $V_{DS} = 480\text{ V}$, $I_D = 11\text{ A}$, $T_j = 125\text{ °C}$ | dv/dt | 50 | V/ns |

Thermal Characteristics

| Parameter | Symbol | Values | | | Unit |
|---|----------------------|--------|------|------|------|
| | | min. | typ. | max. | |
| Thermal resistance, junction - case | R_{thJC} | - | - | 1 | K/W |
| Thermal resistance, junction - case, FullPAK | $R_{thJC\text{ FP}}$ | - | - | 3.8 | |
| Thermal resistance, junction - ambient, leaded | R_{thJA} | - | - | 62 | |
| Thermal resistance, junction - ambient, FullPAK | $R_{thJA\text{ FP}}$ | - | - | 80 | |
| SMD version, device on PCB: @ min. footprint @ 6 cm ² cooling area ³⁾ | R_{thJA} | - | - | 62 | |
| Soldering temperature, 1.6 mm (0.063 in.) from case for 10s ⁴⁾ | T_{sold} | - | - | 260 | °C |

Electrical Characteristics, at $T_j=25\text{ °C}$ unless otherwise specified

| Parameter | Symbol | Conditions | Values | | | Unit |
|---|---------------|--|-------------------|------|------|---------------|
| | | | min. | typ. | max. | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $V_{GS}=0\text{V}$, $I_D=0.25\text{mA}$ | 650 ⁵⁾ | - | - | V |
| Drain-Source avalanche breakdown voltage | $V_{(BR)DS}$ | $V_{GS}=0\text{V}$, $I_D=4\text{A}$ | - | 730 | - | |
| Gate threshold voltage | $V_{GS(th)}$ | $I_D=500\mu\text{A}$, $V_{GS}=V_{DS}$ | 2.1 | 3 | 3.9 | |
| Zero gate voltage drain current | I_{DSS} | $V_{DS}=600\text{V}$, $V_{GS}=0\text{V}$, $T_j=25\text{ °C}$ $T_j=150\text{ °C}$ | - | 0.1 | 1 | μA |
| Gate-source leakage current | I_{GSS} | $V_{GS}=20\text{V}$, $V_{DS}=0\text{V}$ | - | - | 100 | |
| Drain-source on-state resistance | $R_{DS(on)}$ | $V_{GS}=10\text{V}$, $I_D=7\text{A}$ $T_j=25\text{ °C}$ $T_j=150\text{ °C}$ | - | 0.34 | 0.38 | Ω |
| Gate input resistance | R_G | $f=1\text{MHz}$, open drain | - | 0.86 | - | |

Electrical Characteristics

| Parameter | Symbol | Conditions | Values | | | Unit |
|---|--------------|---|--------|------|------|------|
| | | | min. | typ. | max. | |
| Transconductance | g_{fs} | $V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 7A$ | - | 8.3 | - | S |
| Input capacitance | C_{iss} | $V_{GS} = 0V$, $V_{DS} = 25V$, | - | 1200 | - | pF |
| Output capacitance | C_{oss} | $f = 1MHz$ | - | 390 | - | |
| Reverse transfer capacitance | C_{rss} | | - | 30 | - | |
| Effective output capacitance, ⁶⁾ energy related | $C_{o(er)}$ | $V_{GS} = 0V$, $V_{DS} = 0V$ to 480V | - | 45 | - | |
| Effective output capacitance, ⁷⁾ time related | $C_{o(tr)}$ | | - | 85 | - | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD} = 380V$, $V_{GS} = 0/10V$, | - | 10 | - | ns |
| Rise time | t_r | $I_D = 11A$, | - | 5 | - | |
| Turn-off delay time | $t_{d(off)}$ | $R_G = 6.8\Omega$ | - | 44 | 70 | |
| Fall time | t_f | | - | 5 | 9 | |

Gate Charge Characteristics

| | | | | | | |
|-----------------------|-----------------|--|---|-----|----|----|
| Gate to source charge | Q_{gs} | $V_{DD} = 480V$, $I_D = 11A$ | - | 5.5 | - | nC |
| Gate to drain charge | Q_{gd} | | - | 22 | - | |
| Gate charge total | Q_g | $V_{DD} = 480V$, $I_D = 11A$, $V_{GS} = 0$ to 10V | - | 45 | 60 | |
| Gate plateau voltage | $V_{(plateau)}$ | $V_{DD} = 480V$, $I_D = 11A$ | - | 5.5 | - | V |

¹Limited only by maximum temperature

²Repetitive avalanche causes additional power losses that can be calculated as $P_{AV} = E_{AR} \cdot f$.

³Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

⁴Soldering temperature for TO-263: 220°C, reflow

⁵HTRB @ 1000h, 600V, T_{jmax} resp. accelerated HTRB @ 168h, 600V, $T_j = 175^\circ C$
according to JEDEC A108, MIL-STD 750/1038-1040, 1042

⁶ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

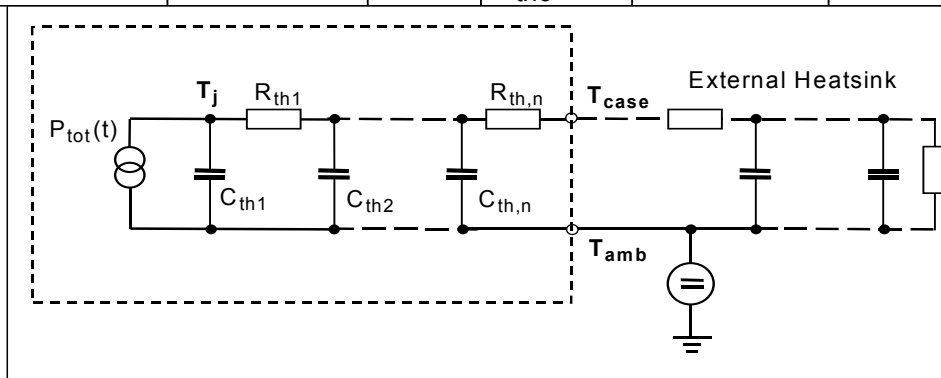
⁷ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

Electrical Characteristics

| Parameter | Symbol | Conditions | Values | | | Unit |
|---|--------------|-----------------------------------|--------|------|------|------------------------|
| | | | min. | typ. | max. | |
| Inverse diode continuous forward current | I_S | $T_C=25^\circ\text{C}$ | - | - | 11 | A |
| Inverse diode direct current, pulsed | I_{SM} | | - | - | 33 | |
| Inverse diode forward voltage | V_{SD} | $V_{GS}=0\text{V}, I_F=I_S$ | - | 1 | 1.2 | V |
| Reverse recovery time | t_{rr} | $V_R=480\text{V}, I_F=I_S,$ | - | 400 | 600 | ns |
| Reverse recovery charge | Q_{rr} | $di_F/dt=100\text{A}/\mu\text{s}$ | - | 6 | - | μC |
| Peak reverse recovery current | I_{rrm} | | - | 41 | - | A |
| Peak rate of fall of reverse recovery current | di_{rr}/dt | $T_j=25^\circ\text{C}$ | - | 1200 | - | $\text{A}/\mu\text{s}$ |

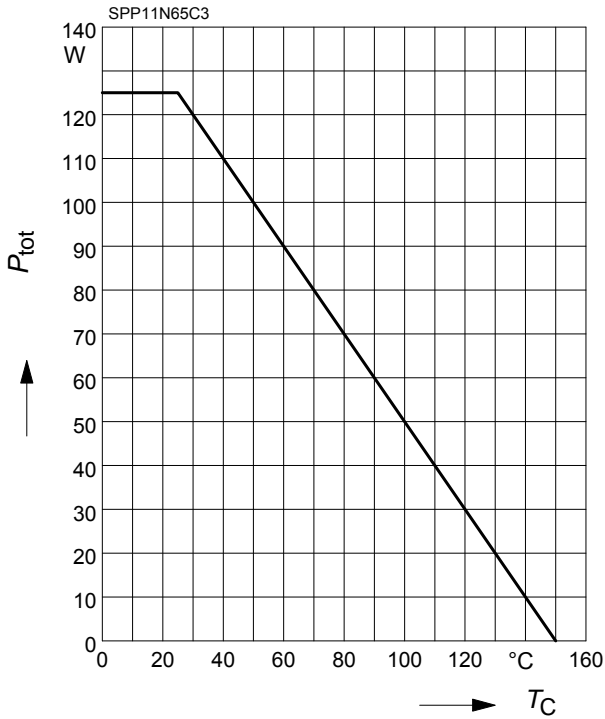
Typical Transient Thermal Characteristics

| Symbol | Value | | Unit | Symbol | Value | | Unit |
|-----------|-------|-------|------|-----------|-----------|-----------|------|
| | SPP_B | SPA | | | SPP_B | SPA | |
| R_{th1} | 0.015 | 0.15 | K/W | C_{th1} | 0.0001878 | 0.0001878 | Ws/K |
| R_{th2} | 0.03 | 0.03 | | C_{th2} | 0.0007106 | 0.0007106 | |
| R_{th3} | 0.056 | 0.056 | | C_{th3} | 0.000988 | 0.000988 | |
| R_{th4} | 0.197 | 0.194 | | C_{th4} | 0.002791 | 0.002791 | |
| R_{th5} | 0.216 | 0.413 | | C_{th5} | 0.007285 | 0.007401 | |
| R_{th6} | 0.083 | 2.522 | | C_{th6} | 0.063 | 0.412 | |



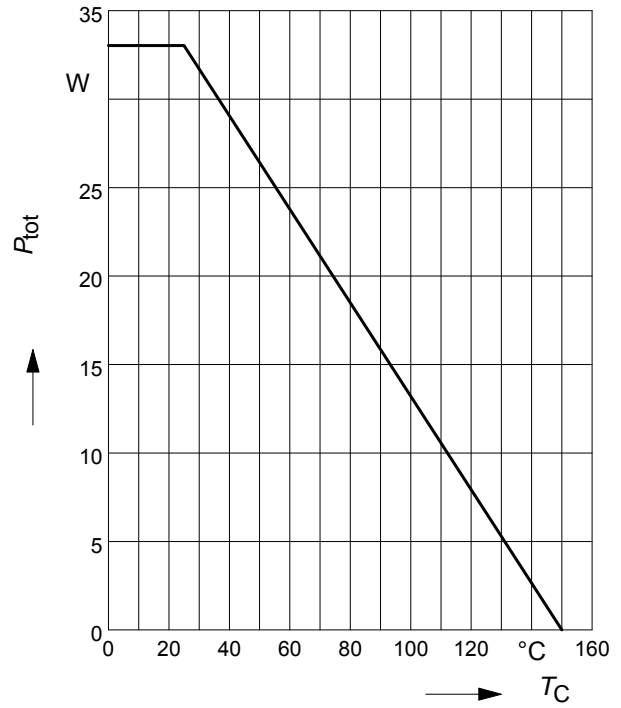
1 Power dissipation

$P_{tot} = f(T_C)$



2 Power dissipation FullPAK

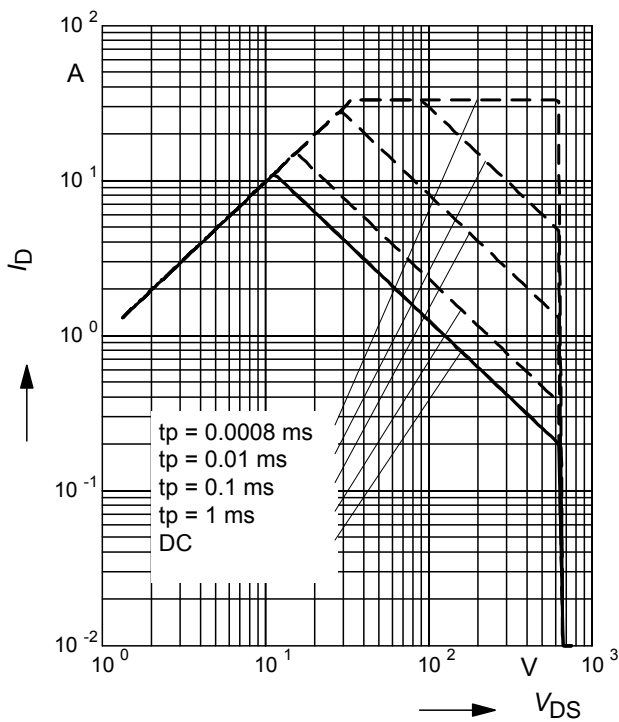
$P_{tot} = f(T_C)$



3 Safe operating area

$I_D = f(V_{DS})$

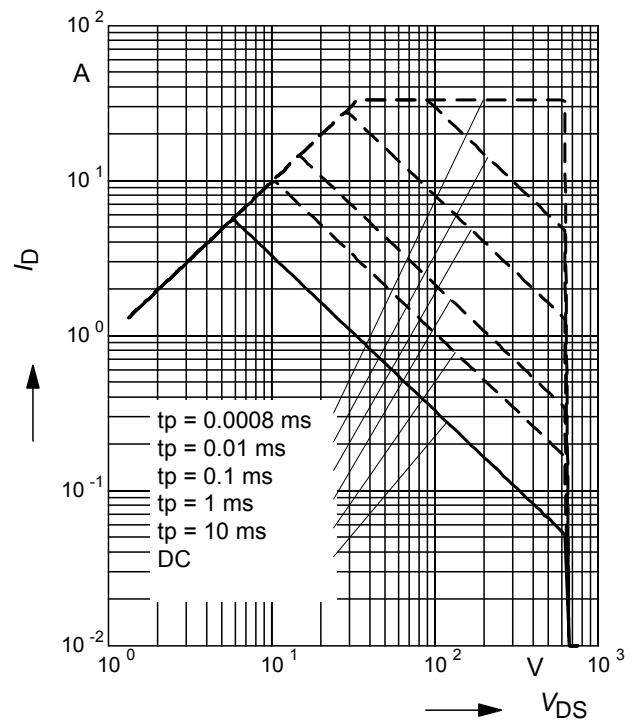
parameter : $D = 0$, $T_C = 25^\circ\text{C}$



4 Safe operating area FullPAK

$I_D = f(V_{DS})$

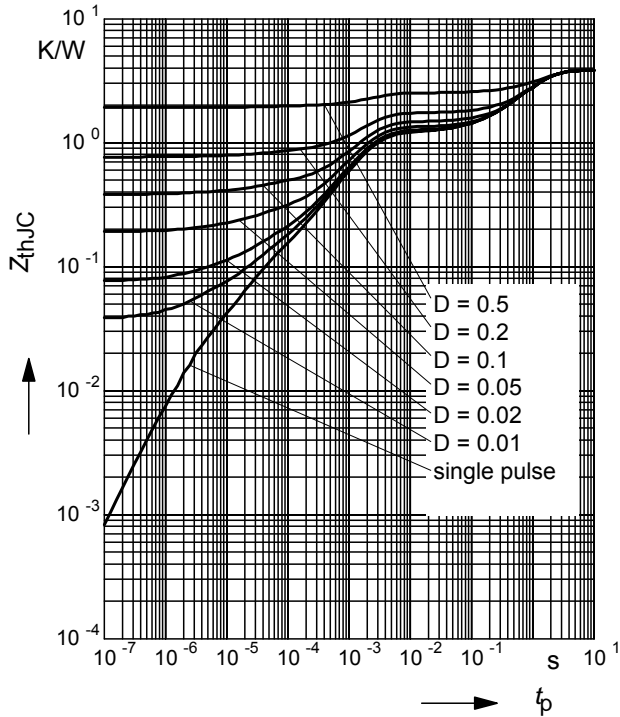
parameter: $D = 0$, $T_C = 25^\circ\text{C}$



5 Transient thermal impedance FullPAK

$Z_{thJC} = f(t_p)$

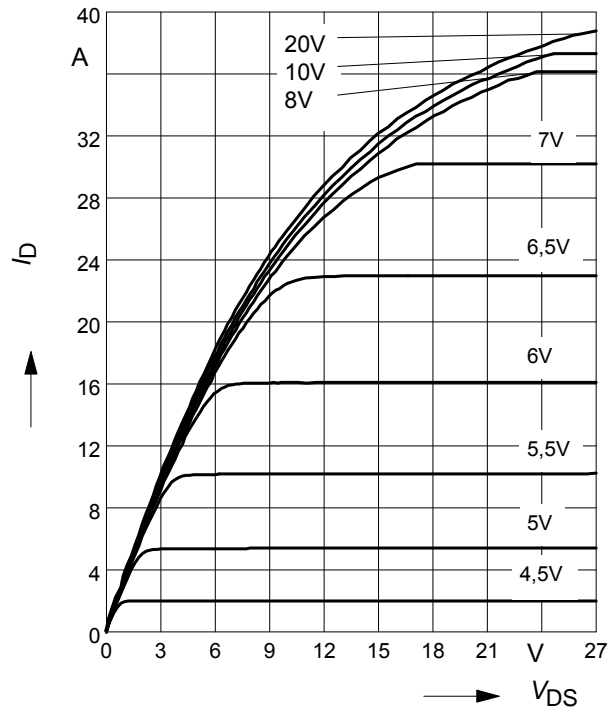
parameter: $D = t_p/t$



6 Typ. output characteristic

$I_D = f(V_{DS}); T_j = 25^\circ C$

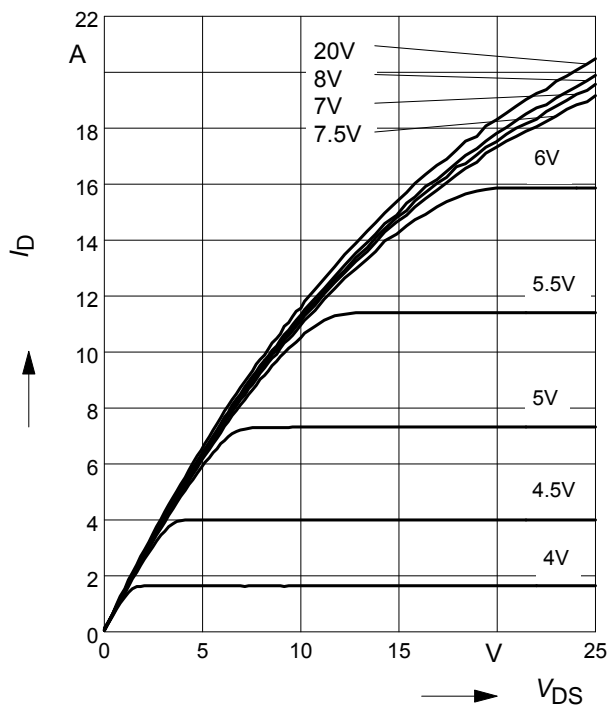
parameter: $t_p = 10 \mu s, V_{GS}$



7 Typ. output characteristic

$I_D = f(V_{DS}); T_j = 150^\circ C$

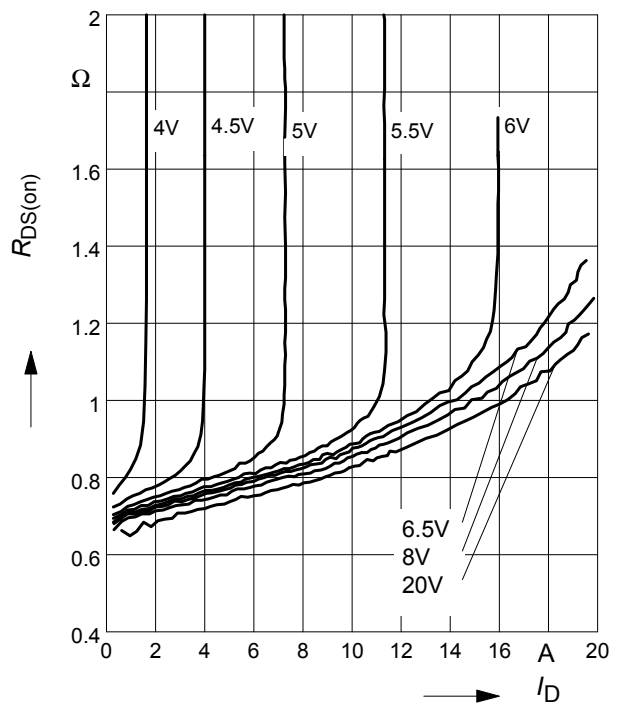
parameter: $t_p = 10 \mu s, V_{GS}$



8 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D)$

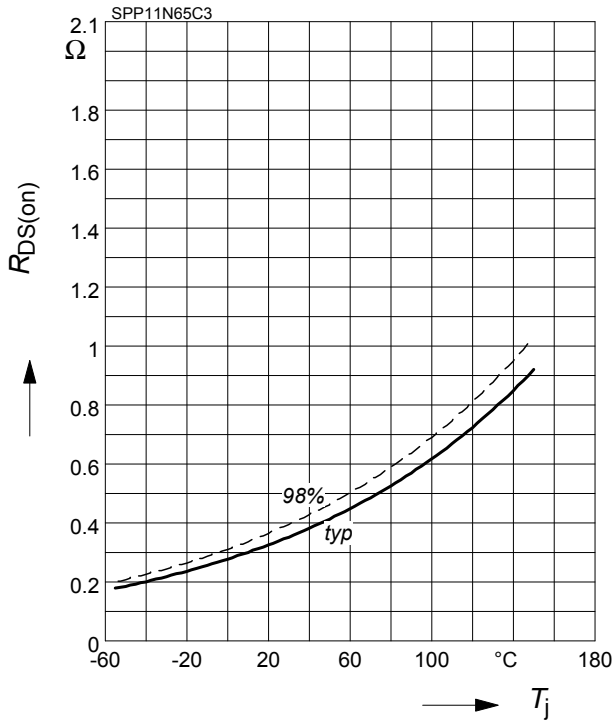
parameter: $T_j = 150^\circ C, V_{GS}$



9 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

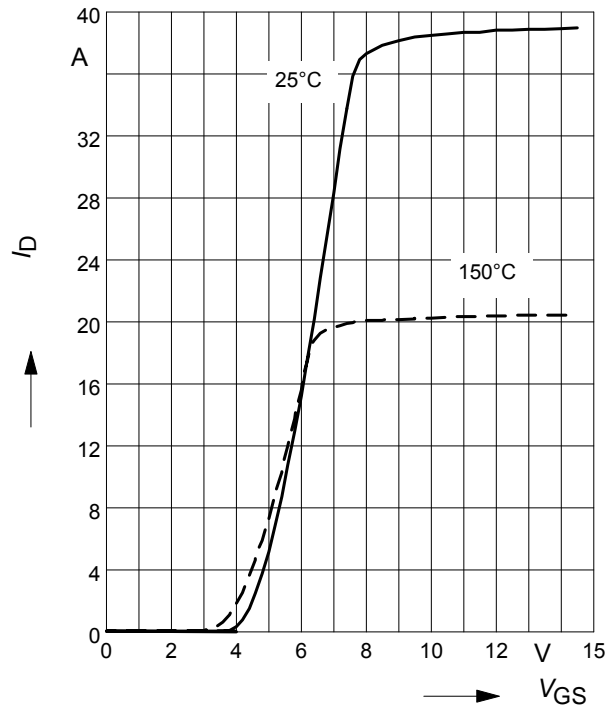
parameter: $I_D = 7\text{ A}$, $V_{GS} = 10\text{ V}$



10 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

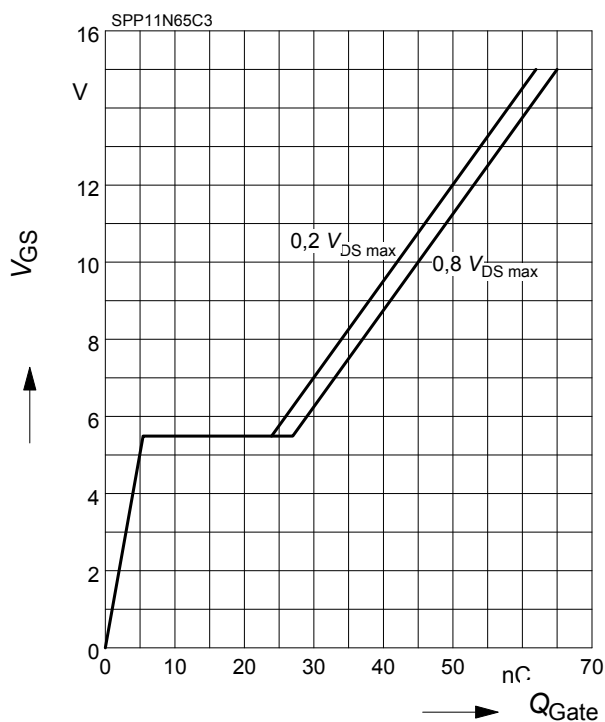
parameter: $t_p = 10\text{ }\mu\text{s}$



11 Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

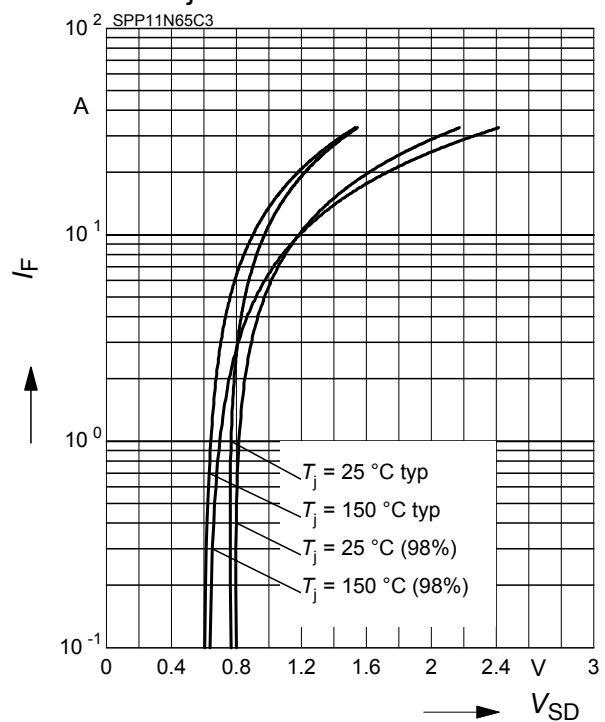
parameter: $I_D = 11\text{ A}$ pulsed



12 Forward characteristics of body diode

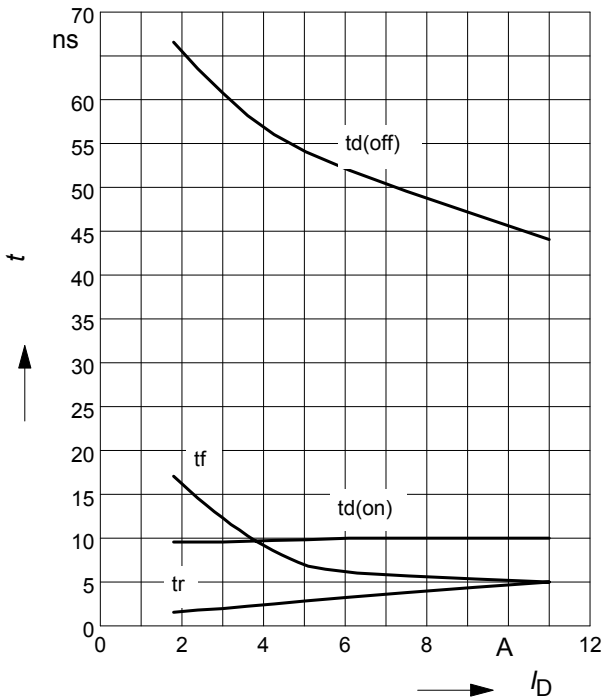
$$I_F = f(V_{SD})$$

parameter: T_j , $t_p = 10\text{ }\mu\text{s}$



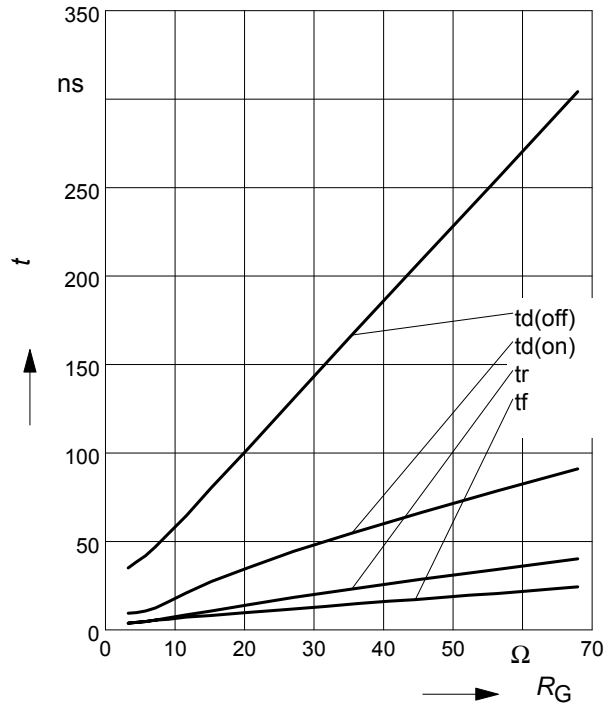
13 Typ. switching time

$t = f(I_D)$, inductive load, $T_j = 125^\circ\text{C}$
par.: $V_{DS} = 380\text{V}$, $V_{GS} = 0/+13\text{V}$, $R_G = 6.8\Omega$



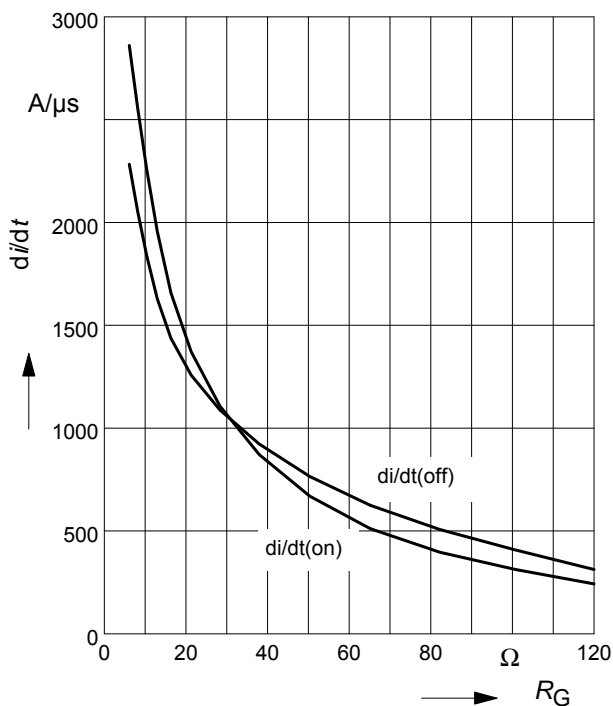
14 Typ. switching time

$t = f(R_G)$, inductive load, $T_j = 125^\circ\text{C}$
par.: $V_{DS} = 380\text{V}$, $V_{GS} = 0/+13\text{V}$, $I_D = 11\text{ A}$



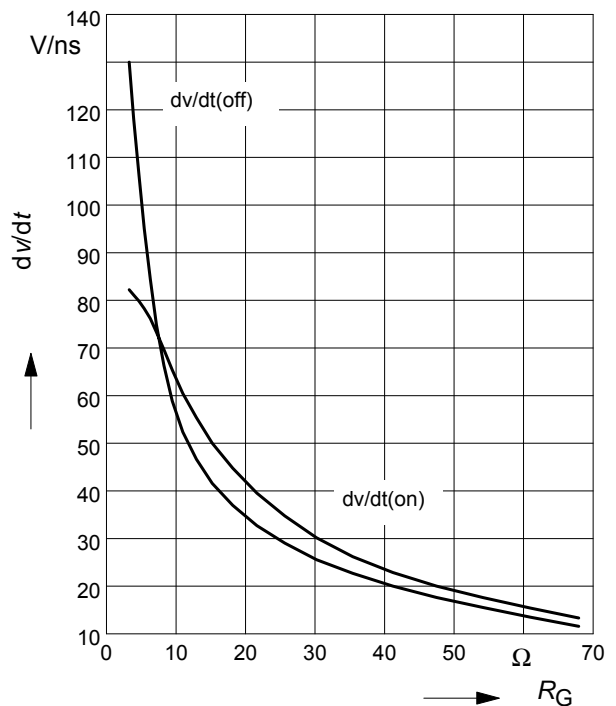
15 Typ. drain current slope

$di/dt = f(R_G)$, inductive load, $T_j = 125^\circ\text{C}$
par.: $V_{DS} = 380\text{V}$, $V_{GS} = 0/+13\text{V}$, $I_D = 11\text{A}$



16 Typ. drain source voltage slope

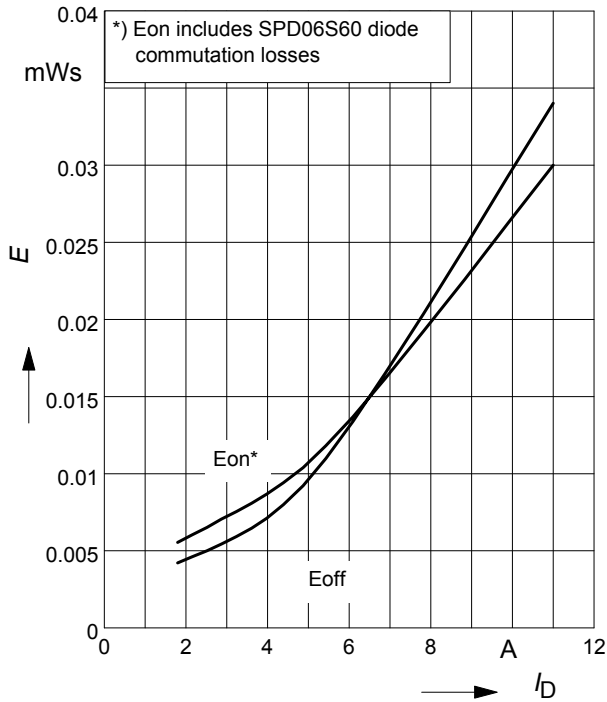
$dv/dt = f(R_G)$, inductive load, $T_j = 125^\circ\text{C}$
par.: $V_{DS} = 380\text{V}$, $V_{GS} = 0/+13\text{V}$, $I_D = 11\text{A}$



17 Typ. switching losses

$E = f(I_D)$, inductive load, $T_j=125^\circ\text{C}$

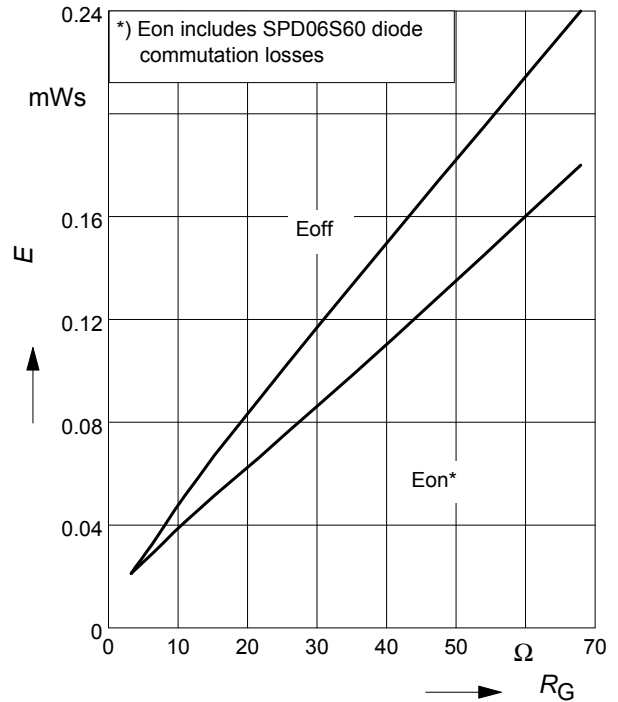
par.: $V_{DS}=380\text{V}$, $V_{GS}=0/+13\text{V}$, $R_G=6.8\Omega$



18 Typ. switching losses

$E = f(R_G)$, inductive load, $T_j=125^\circ\text{C}$

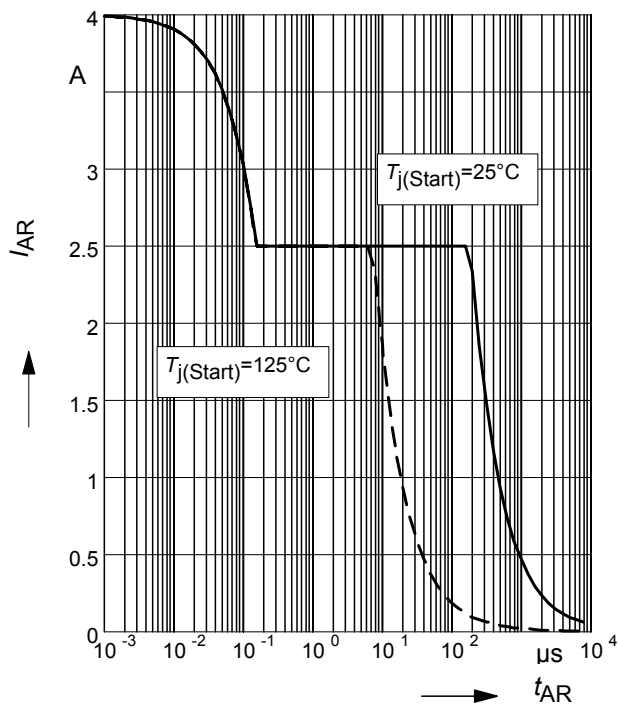
par.: $V_{DS}=380\text{V}$, $V_{GS}=0/+13\text{V}$, $I_D=11\text{A}$



19 Avalanche SOA

$I_{AR} = f(t_{AR})$

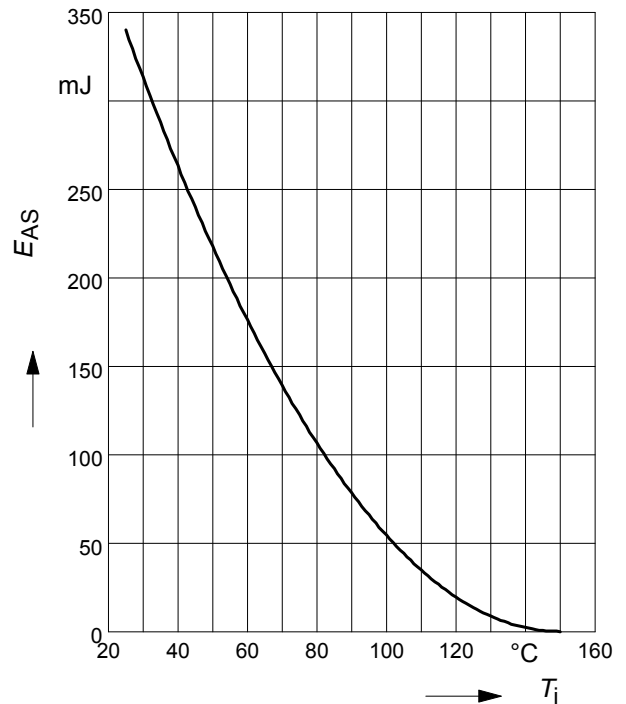
par.: $T_j \leq 150^\circ\text{C}$



20 Avalanche energy

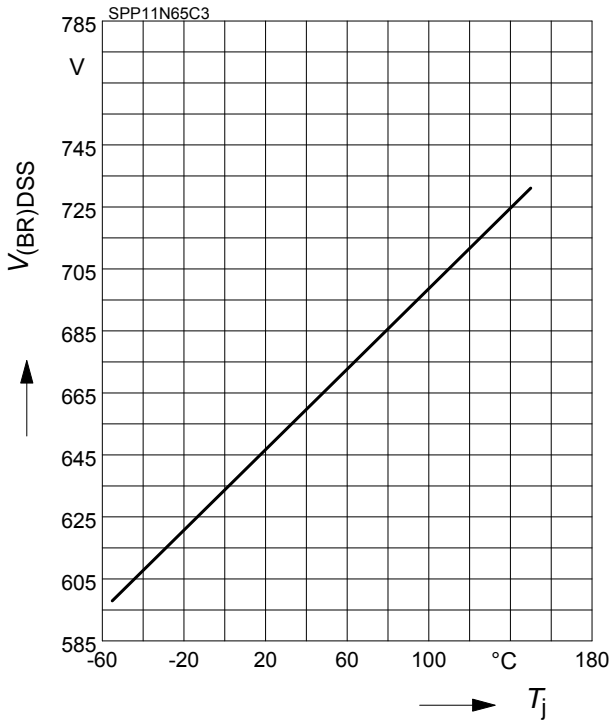
$E_{AS} = f(T_j)$

par.: $I_D = 2.5\text{A}$, $V_{DD} = 50\text{V}$



21 Drain-source breakdown voltage

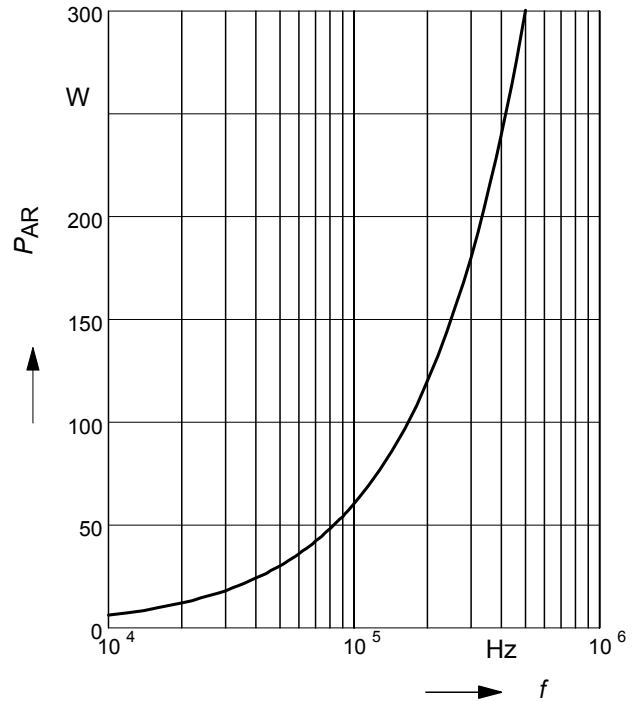
$$V_{(BR)DSS} = f(T_j)$$



22 Avalanche power losses

$$P_{AR} = f(f)$$

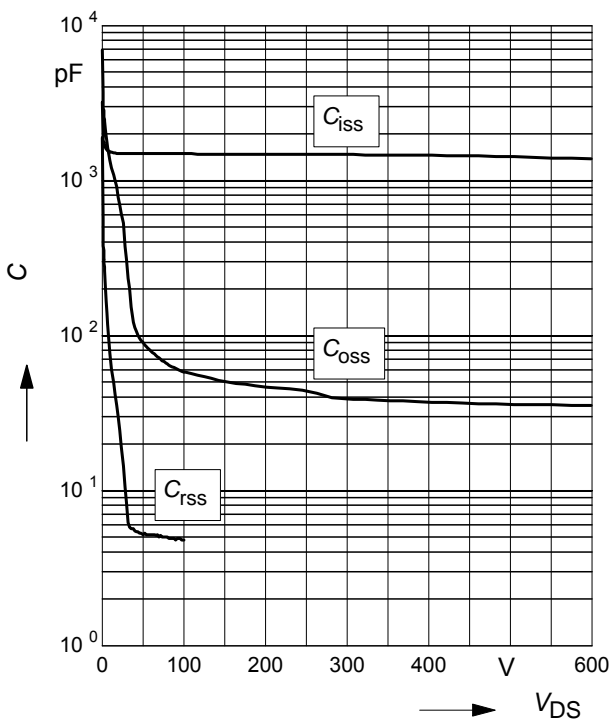
parameter: $E_{AR}=0.6mJ$



23 Typ. capacitances

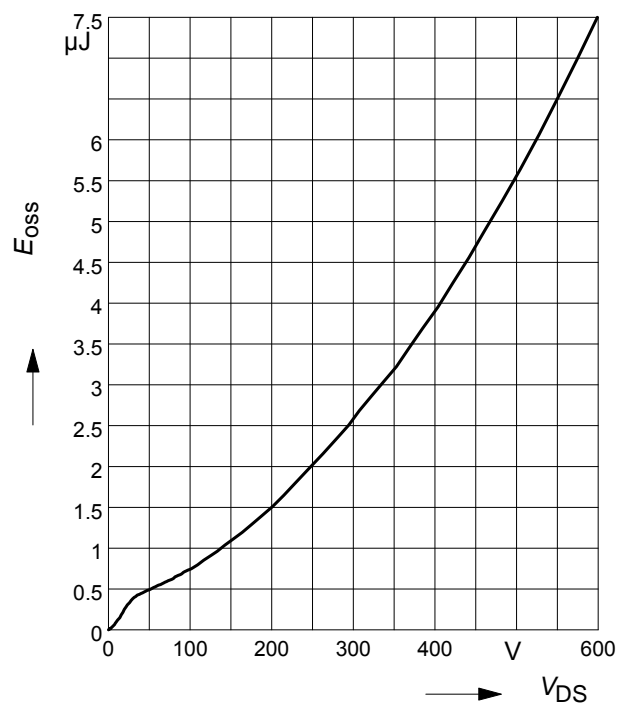
$$C = f(V_{DS})$$

parameter: $V_{GS}=0V, f=1 MHz$

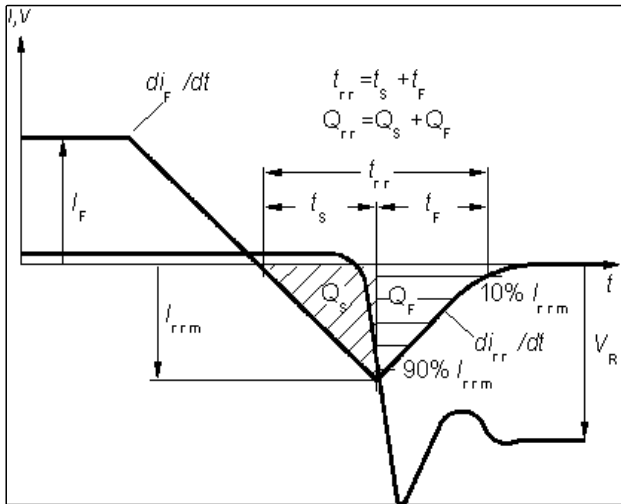


24 Typ. C_{oss} stored energy

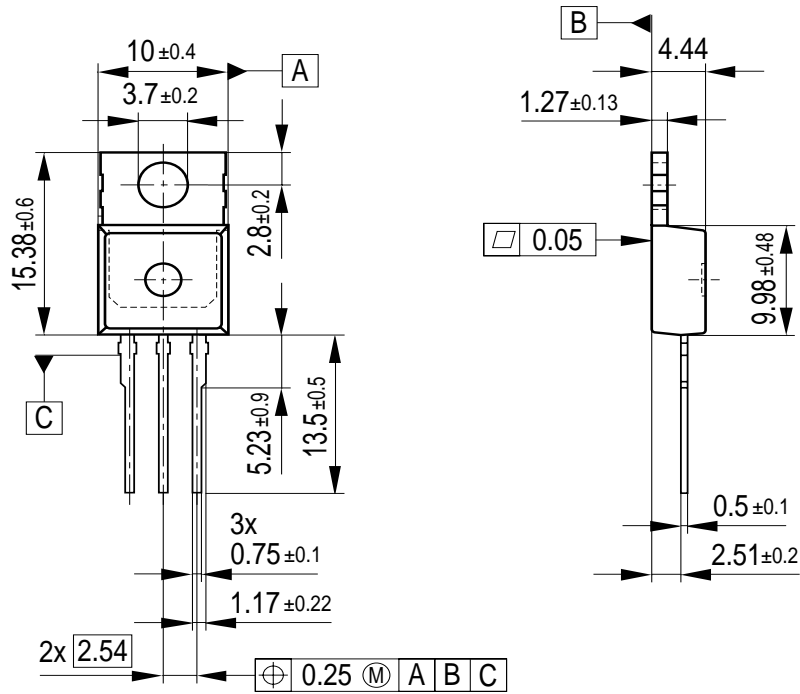
$$E_{oss} = f(V_{DS})$$



Definition of diodes switching characteristics



P-TO-220-3-1



All metal surfaces tin plated, except area of cut.
Metal surface min. $x=7.25$, $y=12.3$

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